

SLPS210B - AUGUST 2009-REVISED OCTOBER 2010

P-Channel NexFET™ Power MOSFET

Check for Samples: CSD25301W1015

FEATURES

- · Ultra Low Qg and Qgd
- Small Footprint
- Low Profile 0.62mm Height
- Pb Free
- RoHS Compliant
- Halogen Free
- CSP 1 x 1.5 mm Wafer Level Package

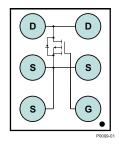
APPLICATIONS

- Battery Management
- Load Switch
- Battery Protection

DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.

Top View



$R_{DS(ON)}$ vs V_{GS} 300 R_{DS(on)} – On-State Resistance – mΩ $I_D = -1A$ 250 200 $T_C = 125^{\circ}C$ 150 100 50 $T_C = 25^{\circ}C$ 0 0 3 5 -V_{GS} - Gate to Source Voltage - V

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	-20	V	
Q_g	Gate Charge Total (4.5V)	1.9	nC	
Q_{gd}	Gate Charge Gate to Drain	0.4	nC	
		$V_{GS} = -1.5V$	175	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -2.5V$	80	mΩ
		V _{GS} = -4.5V	62	mΩ
V _{GS(th)}	Voltage Threshold	-0.75	V	

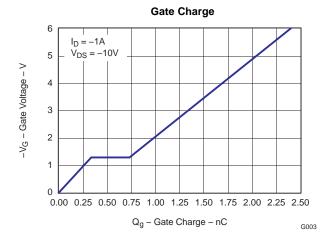
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD25301W1015	1 x 1.5 Wafer Level Package	7-inch reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	Continuous Drain Current, T _C = 25°C ⁽¹⁾	-2.2	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	-8.8	Α
P_D	Power Dissipation ⁽¹⁾	1.5	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

- (1) $R_{\theta JA} = 85$ °C/W on 1in^2 Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

$(1_A = 25)$	°C unless otherwise stated)		1			
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics					
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
I_{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = -16V$			-1	μΑ
I_{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V$, $V_{GS} = \pm 8V$			-100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-0.75	-1	V
		$V_{GS} = -1.5V$, $I_D = -1A$		175	220	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -1A$		80	100	mΩ
		$V_{GS} = -4.5V$, $I_D = -1A$		62	75	mΩ
9 _{fs}	Transconductance	$V_{DS} = -10V, I_{D} = -1A$		5.8		S
Dynamic	Characteristics				,	
C _{ISS}	Input Capacitance			210	270	pF
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$		90	120	pF
C _{RSS}	Reverse Transfer Capacitance			30	40	pF
Q_g	Gate Charge Total (-4.5V)			1.9	2.5	nC
Q_{gd}	Gate Charge Gate to Drain			0.4		nC
Q_{gs}	Gate Charge Gate to Source	$V_{DS} = -10V, I_{D} = -1A$		0.35		nC
Qg(th)	Gate Charge at Vth			0.17		nC
Q _{OSS}	Output Charge	$V_{DS} = -9.8V, V_{GS} = 0V$		1.7		nC
t _{d(on)}	Turn On Delay Time			4		ns
t _r	Rise Time	$V_{DS} = -10V$, $V_{GS} = -4.5V$, $I_{D} = -1A$		2		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 20\Omega$		29		ns
t _f	Fall Time			12		ns
Diode C	haracteristics					
V_{SD}	Diode Forward Voltage	$I_S = -1A$, $V_{GS} = 0V$		-0.75	-1	V
Q _{rr}	Reverse Recovery Charge	$V_{dd} = -9.8V$, $I_F = -1A$, $di/dt = 200A/\mu s$		0.9		nC
t _{rr}	Reverse Recovery Time	$V_{dd} = -9.8V$, $I_F = -1A$, $di/dt = 200A/\mu s$		8.2		ns

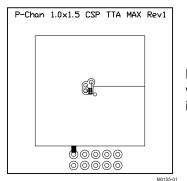
THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

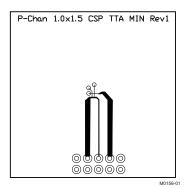
	PARAMETER	MIN	TYP	MAX	UNIT
D	Thermal Resistance Junction to Ambient (Minimum Cu area)			270	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient (1 in ² Cu area)			105	°C/W

Submit Documentation Feedback





Max $R_{\theta JA} = 105^{\circ}\text{C/W}$ when mounted on 1 inch² of 2 oz. Cu.



Max $R_{\theta JA} = 270^{\circ} C/W$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

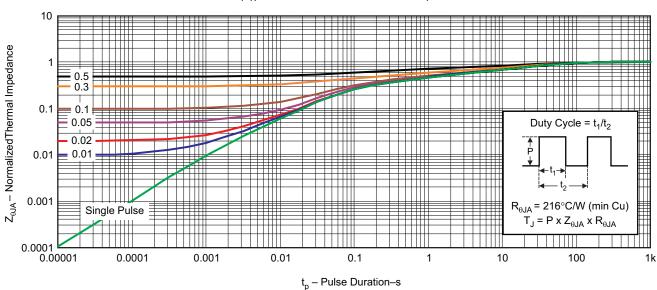


Figure 1. Transient Thermal Impedance

G012



TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

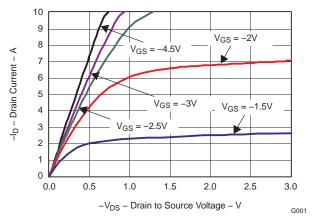


Figure 2. Saturation Characteristics

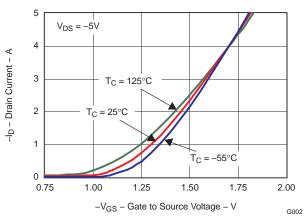


Figure 3. Transfer Characteristics

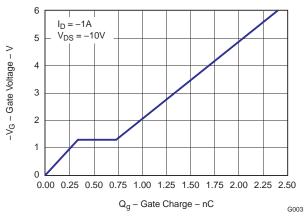


Figure 4. Gate Charge

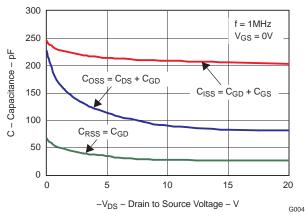


Figure 5. Capacitance

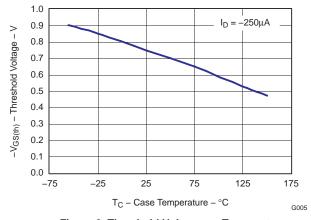


Figure 6. Threshold Voltage vs. Temperature

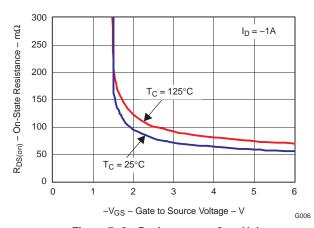


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

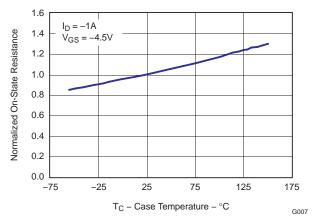


Figure 8. On Resistance vs. Temperature

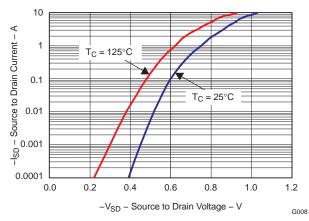


Figure 9. Typical Diode Forward Voltage

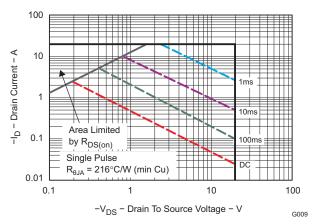


Figure 10. Maximum Safe Operating Area

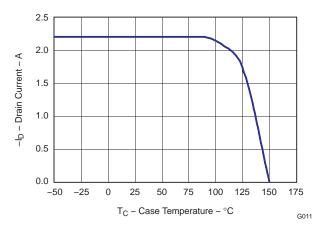
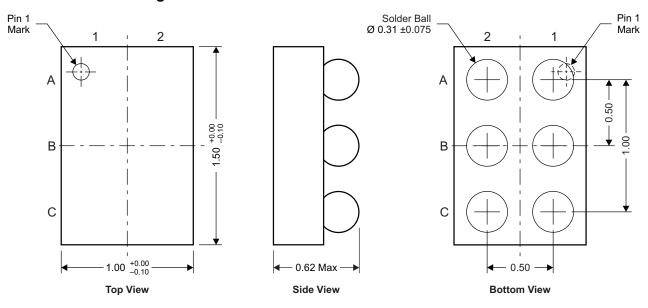


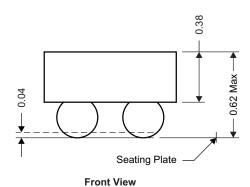
Figure 11. Maximum Drain Current vs. Temperature



MECHANICAL DATA

CSD25301W1015 Package Dimensions





M0157-01

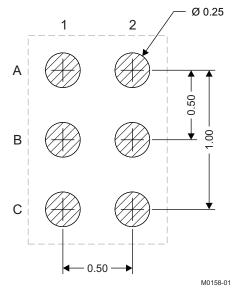
NOTE: All dimensions are in mm (unless otherwise specified)

Pinout

POSITION	DESIGNATION
C1, C2	Drain
A1	Gate
A2, B1, B2	Source

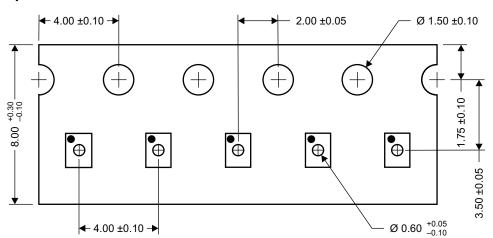


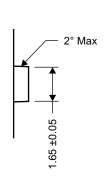
Land Pattern Recommendation

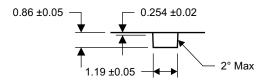


NOTE: All dimensions are in mm (unless otherwise specified)

Tape and Reel Information







M0159-01

NOTE: All dimensions are in mm (unless otherwise specified)

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REVISION HISTORY

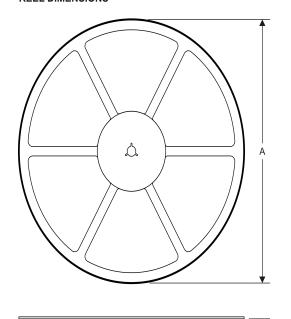
Changes from Original (August 2009) to Revision A	Page
• Replaced incorrect label: R _{θJC} with R _{θJA} in the THERMAL CHARACTERISTICS table	2
Changes from Revision A (August 2010) to Revision B	Page
Deleted the Package Marking Information section	7

PACKAGE MATERIALS INFORMATION

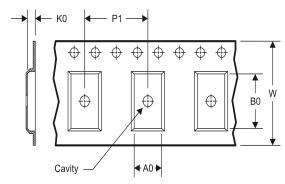
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TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD25301W1015	DSBGA	YZC	6	3000	180.0	8.4	1.09	1.56	0.65	4.0	8.0	Q1

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*All dimensions are nominal

ĺ	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
	CSD25301W1015	DSBGA	YZC	6	3000	210.0	185.0	35.0

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